



News Release

FOR IMMEDIATE RELEASE

Elpida Memory Ships Samples of 2 Gigabit DDR2 SDRAM using 80 nm Process Technology

Industry's Highest Density Memory Devices Using the Smallest, Most Advanced Process Geometry Demonstrates Elpida's Readiness to Support 80 nm Production

TOKYO, JAPAN, December 19, 2005 –Elpida Memory, Inc. (Elpida), Japan's leading global supplier of Dynamic Random Access Memory (DRAM), today announced the shipment of 80 nm-based 2 Gigabit DDR2 SDRAM samples. These samples are among the first 80 nm-based devices in the world to be shipped for customer evaluation, and the devices are expected to be used first in high-density memory modules for high performance servers.

“Inherent in the 80 nm production process technology is the fact that devices using this process will be even smaller in size, although their density is greater,” said Jun Kitano, director of technical marketing for Elpida Memory (USA) Inc. “Based on market demand, Elpida intends to use the 80 nm process for its most advanced DRAM devices at its newly expanded 300 mm wafer manufacturing facility (the E300 Fab) in Hiroshima, Japan.”

Features and Benefits of 2 Gigabit DDR2 SDRAM:

The 2 Gigabit DDR2 SDRAM devices are available in three different data rate speeds: 533 Mega bits per second (Mbps), 667 Mbps, or 800 Mbps. They are organized as either 64 M words x 4 bits x 8 banks or as 32 M words x 8 bits x 8 banks. The supply voltage (VDD) is

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1.8V ± 0.1V, and the operating temperature range (Tc) is 0~85°C. The devices are available in 68-ball FBGA packages for easy mounting on Dual In-line Memory Modules (DIMMs).

Summary of Features

Products	EDE2104AASE-8G-E (DDR2-800) EDE2104AASE-6E-E (DDR2-667) EDE2104AASE-5C-E (DDR2-533) EDE2108AASE-8G-E (DDR2-800) EDE2108AASE-6E-E (DDR2-667) EDE2108AASE-5C-E (DDR2-533)
Process	80 nm (ArF scanner adoption)
Organization	64 M words x 4 bits x 8 banks 32 M words x 8 bits x 8 banks
Supply voltage(VDD)	1.8V ± 0.1V
Data Rate	800 Mbps, 667 Mbps, 533 Mbps
Operating temperature range	Tc = 0~85°C
Package	68-ball FBGA

Elpida originally announced details on the development of 80 nm-based DDR2 SDRAM components on June 23, 2005 ([Elpida Memory Develops 2 Gigabit DDR2 SDRAM Using 80 nm Process Technology for Servers](#)).

Availability

Elpida's 2 Gigabit DDR2 SDRAM devices are currently available to customers as samples and volume production will begin in accordance with market demand.

About Elpida Memory, Inc.

Elpida Memory, Inc. is a manufacturer of Dynamic Random Access Memory (DRAM) silicon chips with headquarters based in Tokyo, Japan, and sales and marketing operations located in Japan, North America, Europe and Asia. Elpida's state-of-the-art semiconductor wafer manufacturing facilities are located in Hiroshima, Japan. Elpida offers a broad range of leading-edge DRAM products for high-end servers, mobile phones, digital television sets and digital cameras as well as personal computers. Elpida had sales of ¥207.0 billion during the fiscal year ending March 31, 2005. For more information, visit www.elpida.com.

The information contained within this news release, is current as of the date of release. Please note that the information herein may be revised later without prior notice.